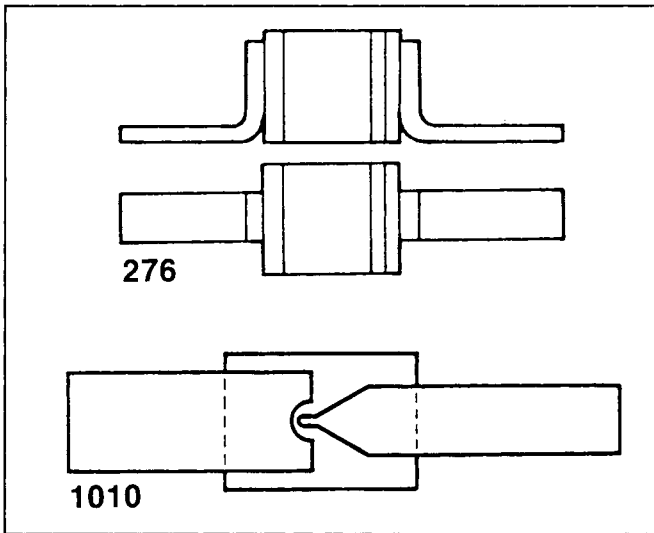




MA40401/MA40422 Series

# GaAs Schottky Mixer Diodes



## Description

This family of Gallium Arsenide Schottky diodes is fabricated with noble metal metallization and silicon nitride passivation to assure good reliability and low series resistance.

These diodes are designed to give superior noise figure from X- through W-band. They are available in a wide range of packages, chip and beam lead configurations. The beam lead types include single beam leads, tees, anti-parallel pairs, and ring and bridge quads.

These diodes have lower series resistance than equivalent junction capacitance silicon schottky diodes. This low series resistance results in superior conversion loss and noise figure.

The higher reverse voltage and low series resistance of Gallium Arsenide Bridge Quads make them particularly attractive for use in AM modulation and/or sampling circuits for signal processing and frequency generation.

## Features

- VERY LOW NOISE FIGURE X, W-BAND
- LOW JUNCTION CAPACITANCE
- LOW SERIES RESISTANCE
- WIDE RANGE OF AVAILABLE PRODUCT

PACKAGED DIODES  
CHIPS  
BEAM LEADS  
ANTI-PARALLEL BEAM LEADS  
BRIDGE QUADS  
RING QUADS  
TEES

- SUPERIOR DYNAMIC RANGE TO SILICON DIODES
- MINIMUM BREAKDOWN VOLTAGE IS 5 VOLTS
- MINIMUM 10 GRAM BEAM STRENGTH FOR BEAM LEADS

**MAXIMUM RATINGS**

Operating and Storage Temperature Range of Junctions	-65° to 150°C
Maximum Power Dissipation (Derate Linearity to Zero at 150°C)	at 25°C 75 mW/Junction
Soldering Temperature (Packaged Diodes)	235°C for 10 seconds
Beam Strength	10 Grams Min.

**Specifications @ T<sub>A</sub> = 25°C****PACKAGED DIODES**

SPECIFICATIONS						TYPICAL CHARACTERISTICS	
Model <sup>9</sup> Number	Case Style	L.O. Test Frequency (GHz)	Maximum <sup>4</sup> Noise Figure NF (dB)	IF <sup>4</sup> Impedance Min./Max. (Ohms)	Minimum <sup>5</sup> Breakdown Voltage V <sub>B</sub>	Nominal <sup>1,8</sup> Junction Capacitance C <sub>j</sub> (pF)	Nominal <sup>3</sup> Series Resistance R <sub>S</sub> (Ohms)
MA40401	119	9.375	5.7	250 / 500	5	.10	3/6
MA40402	119	16.000	6.0	250 / 500	5	.10	3/6
MA40403	119	24.000	6.5	250 / 500	5	.07	3/6
MA40404	119	36.000	6.5	250 / 500	5	.06	3/6
MA40405	120	9.375	5.7	250 / 500	5	.10	3/6
MA40406	120	16.000	6.0	250 / 500	5	.10	3/6
MA40407	120	24.000	6.5	250 / 500	5	.07	3/6
MA40408	120	36.000	6.5	250 / 500	5	.06	3/6
MA40409	276	9.375	5.7	250 / 500	5	.10	3/6
MA40410	276	16.000	6.0	250 / 500	5	.10	3/6
MA40411	276	24.000	6.5	250 / 500	5	.07	3/6
MA40412	276	36.000	6.5	250 / 500	5	.06	3/6

**BEAM LEADS AND CHIPS**

SPECIFICATIONS						TYPICAL CHARACTERISTICS	
Model <sup>9</sup> Number	Case Style	Frequency Band	Series <sup>3</sup> Resistance Min./Max. (Ohms)	Junction <sup>1</sup> Capacitance Min./Max. (pF)	Minimum <sup>5</sup> Breakdown Voltage (Volts)	IF Impedance Min./Max. (Ohms)	Nominal Noise Figure (dB)
MA40413	135	X-K	3/6	.055 / .075	5	250 / 500	6.0
MA40414	135	Ka	3/6	.050 / .060	5	250 / 500	6.5
MA40415	1010	K	3/6	.055 / .075	5	250 / 500	6.5
MA40416	1010	Ka	3/6	.050 / .070	5	250 / 500	6.5
MA40417	1010	W	4/10	.030 / .055	5	250 / 500	7 <sup>10</sup>

**ANTI-PARALLEL BEAM LEADS**

SPECIFICATIONS								TYPICAL CHARACTERISTICS
Model Number	Case Style	Frequency Band	Series <sup>3</sup> Resistance Min./Max. R <sub>S</sub> (Ohms)	Junction <sup>6</sup> Capacitance Min./Max. C <sub>j</sub> (pF)	Maximum <sup>6</sup> Junction Capacitance Difference ΔC <sub>j</sub> (pF)	Minimum <sup>5</sup> Breakdown Voltage V <sub>B</sub> (Volts)	Maximum <sup>2</sup> Forward Voltage Difference ΔV <sub>F</sub> (Volts)	Nominal <sup>2</sup> Forward Voltage V <sub>F</sub> (Volts)
MA40422	1013	K-Ka	3/6	.10 / .20	.025	5.0	.015	.700

# Specifications @ $T_A = 25^\circ\text{C}$

## PACKAGED TEES AND QUADS

### Bridge Quad

SPECIFICATIONS								TYPICAL CHARACTERISTICS
Model Number	Case Style	Frequency Band	Maximum <sup>3</sup> Series Resistance Min./Max. $R_S$ (Ohms)	Junction <sup>7,8</sup> Capacitance Min./Max. $C_j$ (pF)	Maximum <sup>7,8</sup> Junction Capacitance Difference $\Delta C_j$ (pF)	Minimum <sup>5</sup> Breakdown Min./Max. $V_B$ (Volts)	Maximum <sup>2</sup> Forward Voltage Difference $\Delta V_F$ (Volts)	Nominal <sup>2</sup> Forward Voltage $V_F$ (Volts)
MA40418	963	L-K	3/6	.05 / .10	.025	6	.020	.700

### Ring Quad

SPECIFICATIONS								TYPICAL CHARACTERISTICS
Model Number	Case Style	Frequency Band	Maximum <sup>3</sup> Series Resistance Min./Max. $R_S$ (Ohms)	Junction <sup>7,8</sup> Capacitance Min./Max. $C_j$ (pF)	Maximum <sup>7,8</sup> Junction Capacitance Difference $\Delta C_j$ (pF)	Minimum <sup>5</sup> Breakdown Min./Max. $V_B$ (Volts)	Maximum <sup>2</sup> Forward Voltage Difference $\Delta V_F$ (Volts)	Nominal <sup>2</sup> Forward Voltage $V_F$ (Volts)
MA40419	963	L-K	3/6	.05 / .10	.025	5.0	.020	.700

### Tees

SPECIFICATIONS							TYPICAL CHARACTERISTICS		
Model Number	Case Style	Frequency Band	Maximum <sup>3</sup> Series Resistance Min./Max. $R_S$ (Ohms)	Junction <sup>7,8</sup> Capacitance Min./Max. $C_j$ (pF)	Maximum <sup>7,8</sup> Junction Capacitance Difference $\Delta C_j$ (pF)	Maximum <sup>2</sup> Forward Voltage Difference $\Delta V_F$ (Volts)	Nominal <sup>2</sup> Forward Voltage $V_F$ (Volts)	Nominal <sup>5</sup> Breakdown Voltage $V_B$ (Volts)	Nominal <sup>4</sup> Noise Figure $N_f$ (dB)
MA40420	270	C-Ku	3/6	.05 / .10	.025	.020	.700	5	6
MA40421	272	C-Ku	3/6	.05 / .10	.025	.020	.700	5	6

#### NOTES:

- $C_j$  is measured at  $V_r = 0V$  and  $F = 1.0$  MHz.
- $V_f$  is measured at  $I_f = 1.0$  mA.
- Series Resistance,  $R_S$ , is determined by subtracting the junction resistance  $R_j$ , from the measured value of 10 mA dynamic (slope) resistance,  $R_d$ :  

$$R_S = R_d - R_j \text{ ohms}$$
 Junction resistance is computed from:  

$$R_j = 26/I_f$$

$$I_f = 10 \text{ mA}$$

$$I_f \text{ is the forward current in mA}$$
- Noise figure measurements are single sideband noise figure with  $N_{ff} = 1.5$  dB minimum. The noise figure of chips and beam lead types are performed on a sample of the lot. Chips are tested in a package. Beam leads are tested in a stripline holder. The test conditions are as follows:
- $V_B$  is measured at  $I_r = 10 \mu\text{A}$ .
- $C_j$  is measured at  $V_r = 0V$  and  $F = 1.0$  MHz.  $C_j$  of anti-parallel diodes is comprised of the capacitance of two diode junctions in parallel.
- $C_j$  is measured between adjacent leads of device at  $V_r = 0V$  and  $F = 1.0$  MHz.
- $C_t = C_j + C_p$   
 $C_t$  is total capacitance  
 $C_j$  is junction capacitance  
 $C_p$  is packaged capacitance
- Match pairs are available by adding the suffix "M" to the part number.
- Conversion loss at 94 GHz with  $L_o$  power  $\sim 8$ -12 dBm.

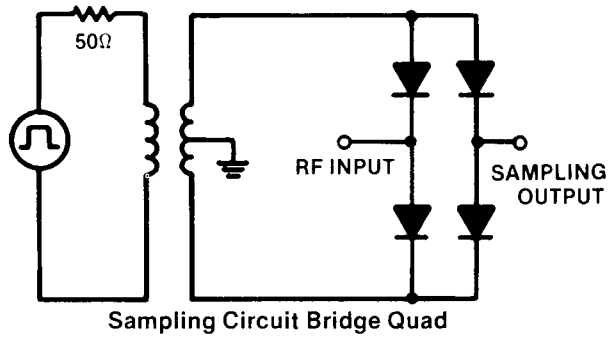
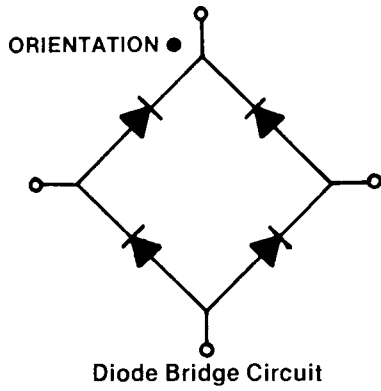
L.O. Power      6.0 dBm  
 L.O. Frequency    3.0 GHz  
                       9.375 GHz  
                       16.0 GHz  
                       24.0 GHz  
                       35.0 GHz

$f_{if} = 30$  MHz  
 $R_l = 22$  ohms

# Packaged Quad and Tee Configurations

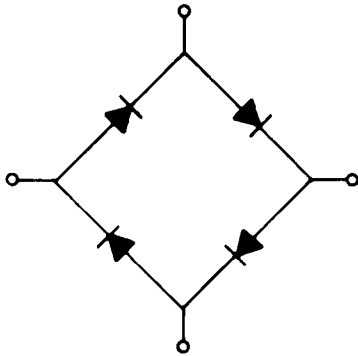
## BRIDGE QUAD CIRCUIT

TOP VIEW PACKAGE

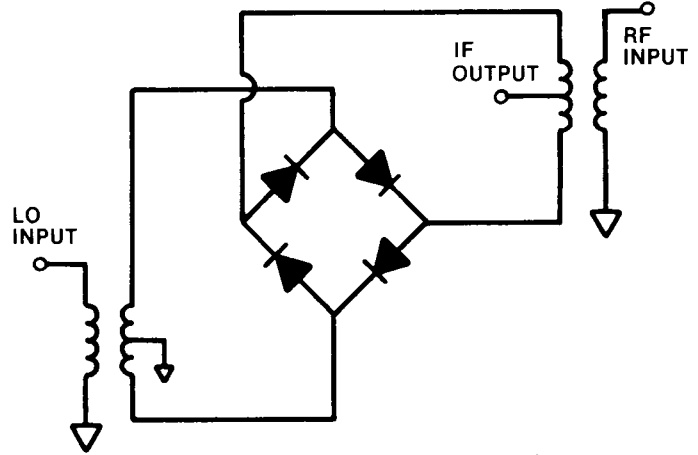


## RING QUAD CIRCUIT

TOP VIEW PACKAGE

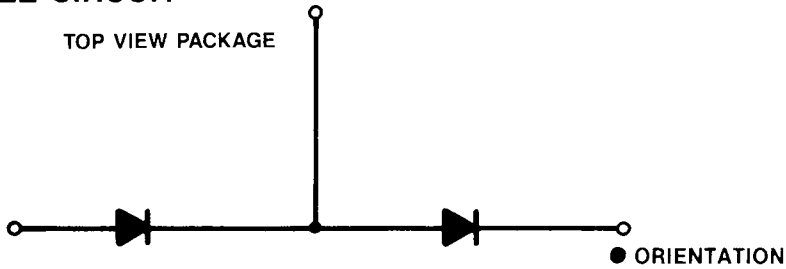


Double Balanced Mixer Ring Quad Circuit

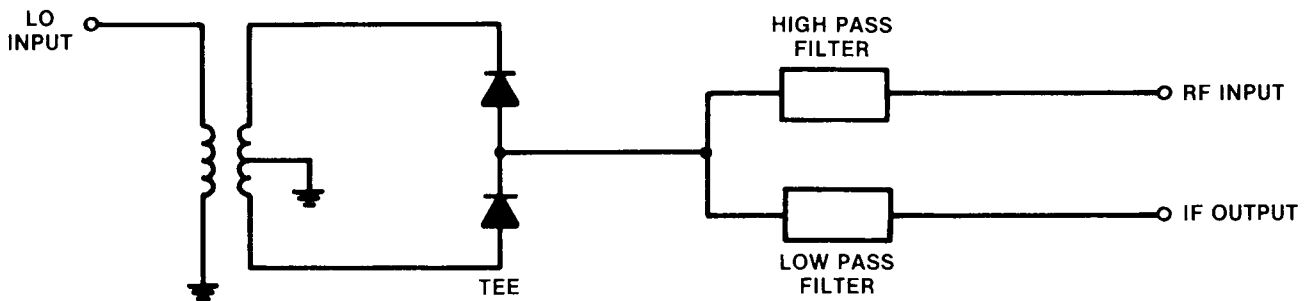


## TEE CIRCUIT

TOP VIEW PACKAGE

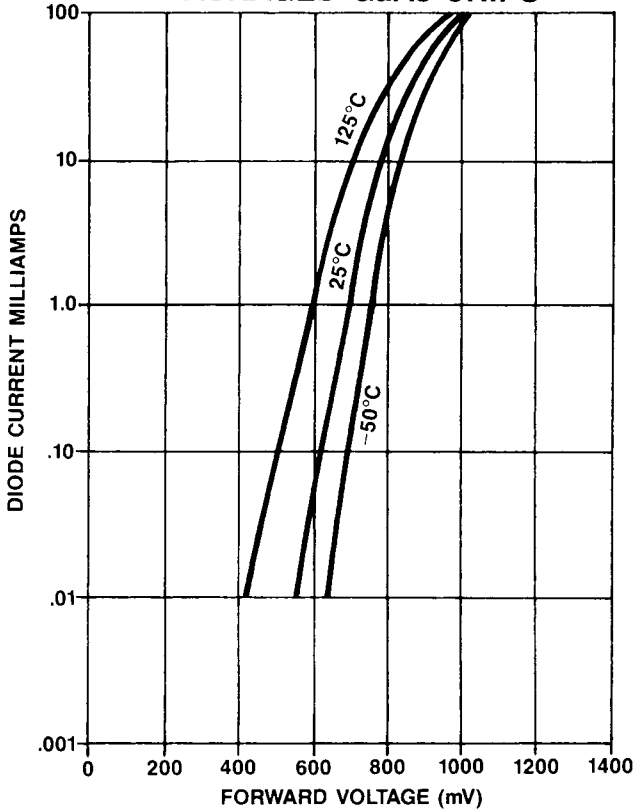


## BALANCED MIXER

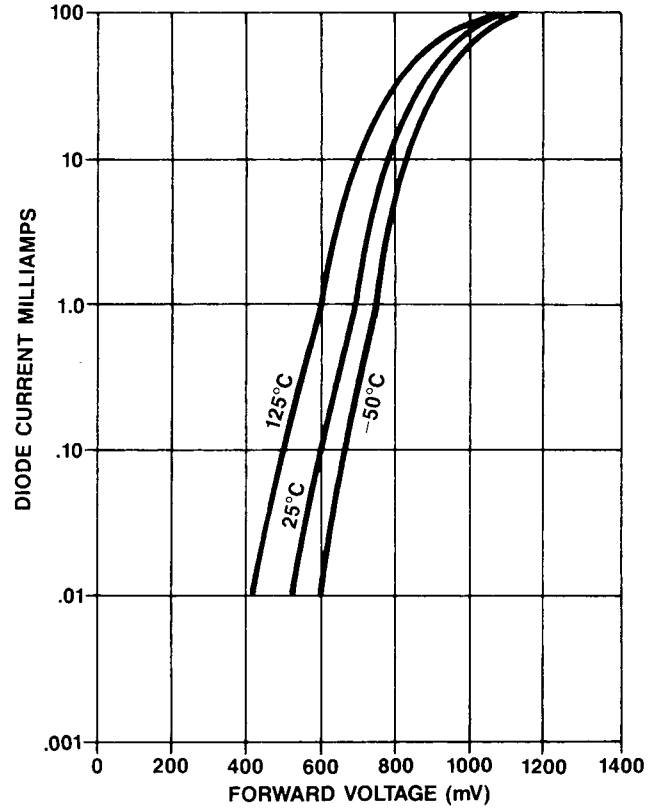


# Typical Performance Curves

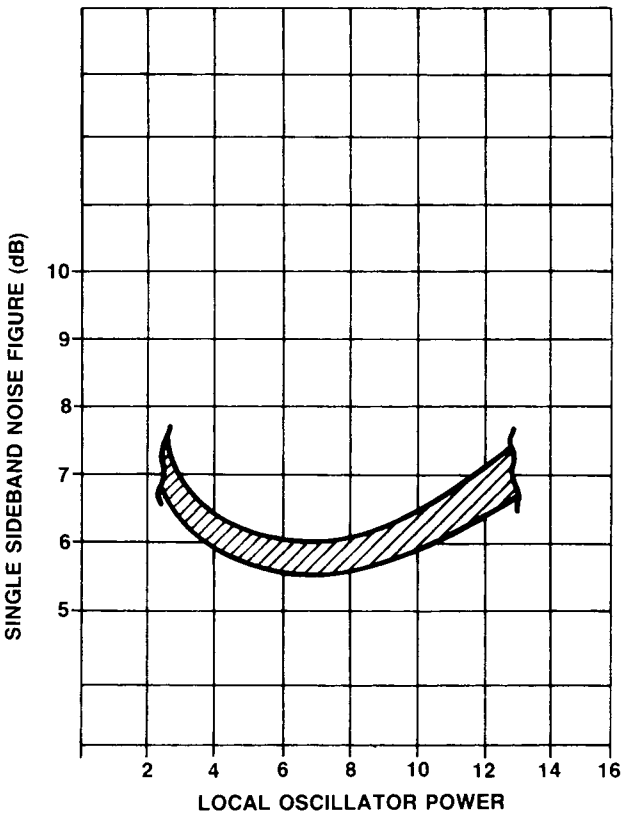
**MA40401-40412  
PACKAGED GaAs CHIPS**



**MA40413  
GaAs BEAM LEAD**

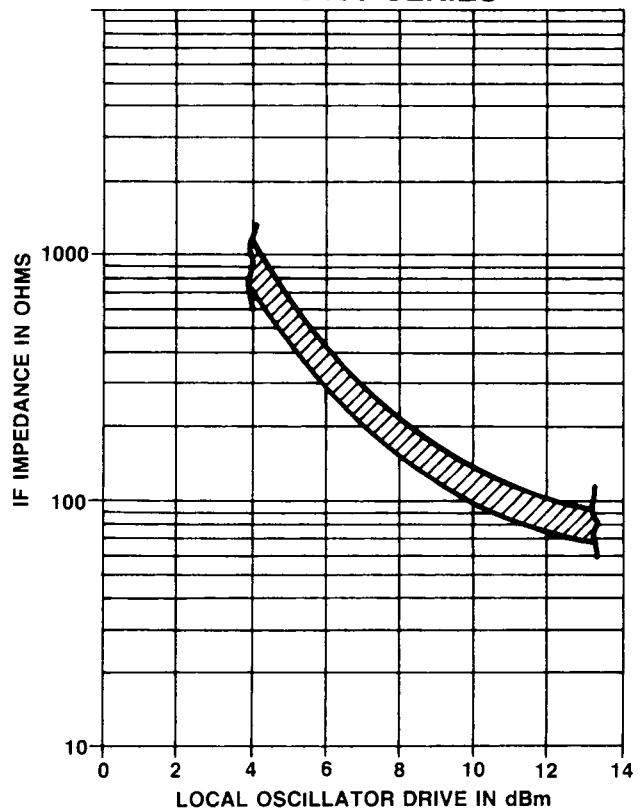


**MA-40400 SERIES**



NOISE FIGURE VS. LOCAL OSCILLATOR POWER

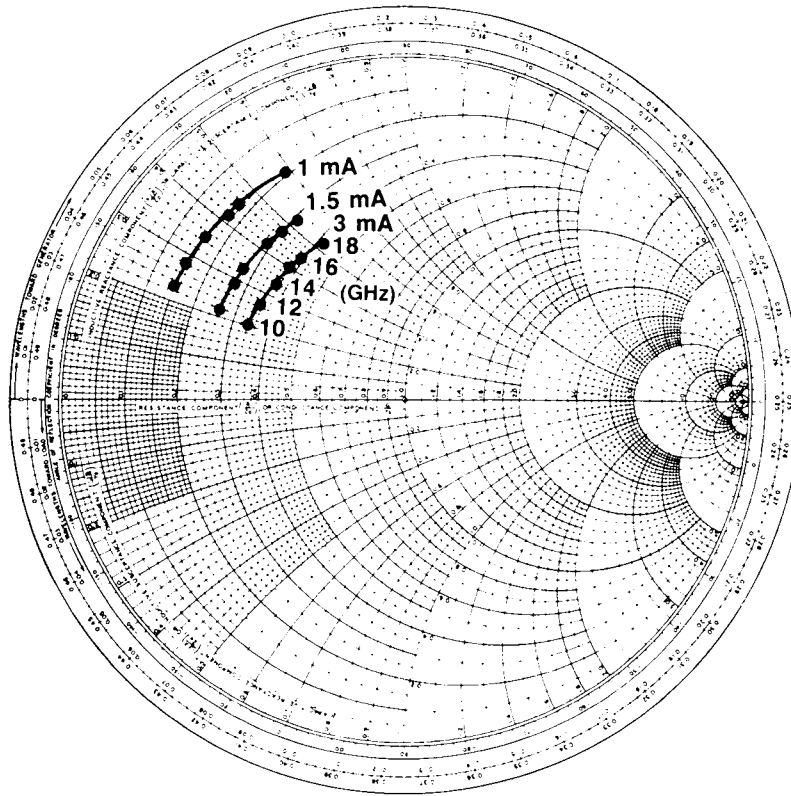
**MA40400 SERIES**



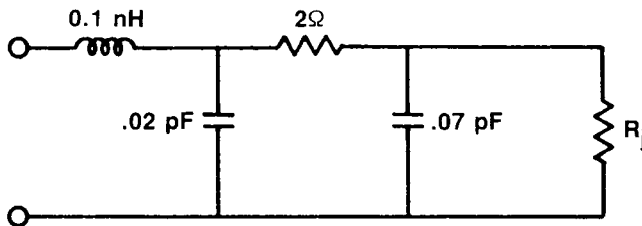
IF IMPEDANCE VS. LOCAL OSCILLATOR DRIVE WITH  $R_L = 10$  OHMS

# Typical Admittance Characteristics With Self Bias

MA40413 CHIP OR MA40415 BEAM LEAD



Approximate Equivalent Circuit of MA40415



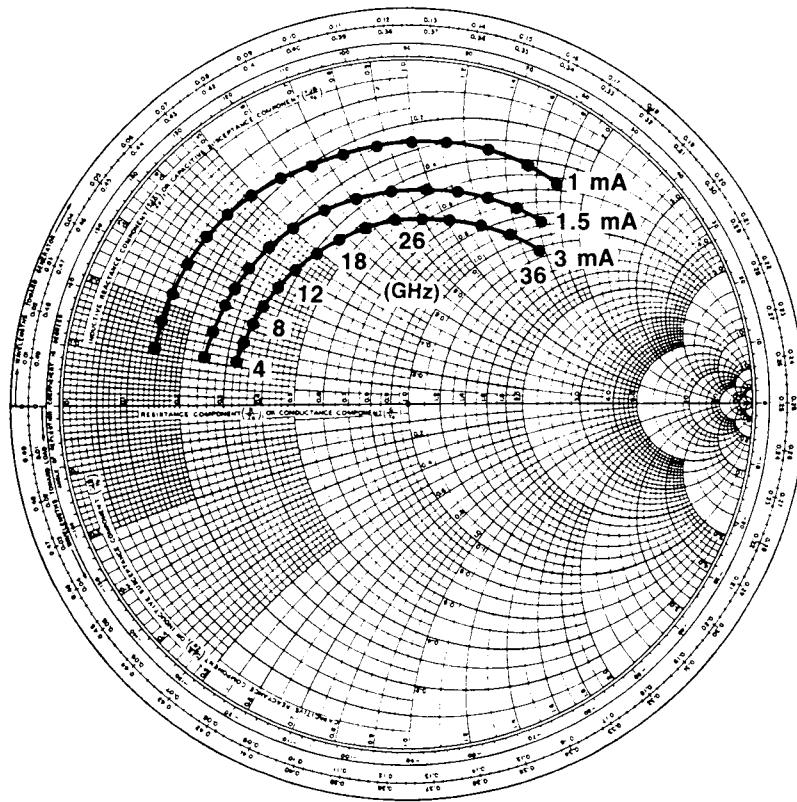
SELF BIAS (mA)	$R_j$ (ohms)
1.0	350
1.5	200
3.0	150

Typical RF Impedance Data

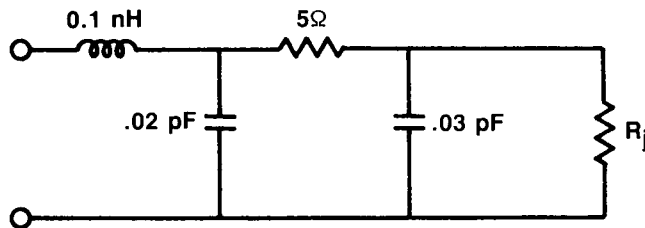
Frequency (GHz)	1.0 mA		1.5 mA		3.0 mA	
	Refl Mag	Coeff Ang	Refl Mag	Coeff Ang	Refl Mag	Coeff Ang
4	.751	- 13.0	.603	- 13.2	.505	- 13.6
6	.751	- 19.6	.603	- 19.9	.506	- 20.4
8	.751	- 26.1	.604	- 26.6	.506	- 27.2
10	.750	- 32.8	.604	- 33.4	.507	- 34.2
12	.750	- 32.8	.604	- 40.2	.508	- 41.2
14	.750	- 46.2	.606	- 47.1	.510	- 48.2
16	.750	- 53.1	.607	- 54.1	.512	- 55.4
18	.751	- 60.0	.609	- 61.1	.515	- 62.6
20	.751	- 67.0	.611	- 68.3	.519	- 69.9
22	.753	- 74.1	.614	- 75.5	.523	- 77.3
24	.754	- 81.3	.618	- 82.7	.529	- 84.7
26	.756	- 88.5	.623	- 90.1	.536	- 92.1
28	.759	- 95.7	.629	- 97.4	.543	- 99.5
30	.762	- 103.0	.636	- 104.7	.552	- 107.0
32	.766	- 110.3	.643	- 112.1	.562	- 114.3
34	.771	- 117.5	.652	- 119.3	.574	- 121.6
36	.776	- 124.7	.662	- 126.6	.586	- 128.8

# Typical Admittance Characteristics With Self Bias

## MA40417 BEAM LEAD



Approximate Equivalent Circuit of MA40417



SELF BIAS (mA)	$R_j$ (ohms)
1.0	350
1.5	200
3.0	150

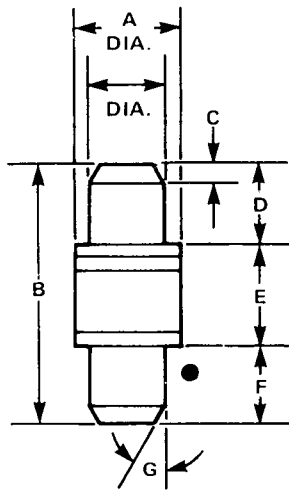
Typical RF Impedance Data

Frequency (GHz)	1.0 mA		1.5 mA		3.0 mA	
	Refl Mag	Coeff Ang	Refl Mag	Coeff Ang	Refl Mag	Coeff Ang
4	.752	- 7.1	.607	- 7.1	.511	- 7.1
6	.751	- 10.7	.606	- 10.7	.510	- 10.6
8	.750	- 14.3	.604	- 14.3	.508	- 14.2
10	.749	- 18.0	.602	- 17.9	.506	- 17.9
12	.747	- 21.7	.600	- 21.6	.503	- 21.6
14	.744	- 25.5	.597	- 25.4	.500	- 25.4
16	.742	- 29.3	.593	- 29.2	.496	- 29.3
18	.739	- 33.2	.590	- 33.1	.492	- 33.2
20	.735	- 37.2	.586	- 37.2	.488	- 37.3
22	.732	- 41.4	.581	- 41.3	.483	- 41.5
24	.728	- 45.6	.577	- 45.6	.478	- 45.8
26	.724	- 49.9	.572	- 50.0	.472	- 50.3
28	.720	- 54.4	.567	- 54.6	.467	- 55.0
30	.716	- 59.1	.562	- 59.3	.462	- 59.8
32	.711	- 63.9	.557	- 64.2	.456	- 64.9
34	.707	- 68.8	.552	- 69.3	.451	- 70.1
36	.703	- 73.9	.547	- 74.5	.447	- 75.6

# Case Styles

● DENOTES CATHODE

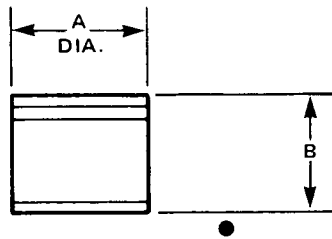
119



DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.078	0.086	1,98	2,18
B	0.190	0.210	4,83	5,33
C	0.009	0.015	0,23	0,38
D	0.060	0.064	1,52	1,63
E	0.070	0.087	1,68	2,21
F	0.060	0.064	1,52	1,63
G	25°	35°	25°	35°
H	0.060	0.064	1,52	1,63

C<sub>P</sub> = 0.15 pF Typical  
L<sub>S</sub> = 0.50 nH Typical

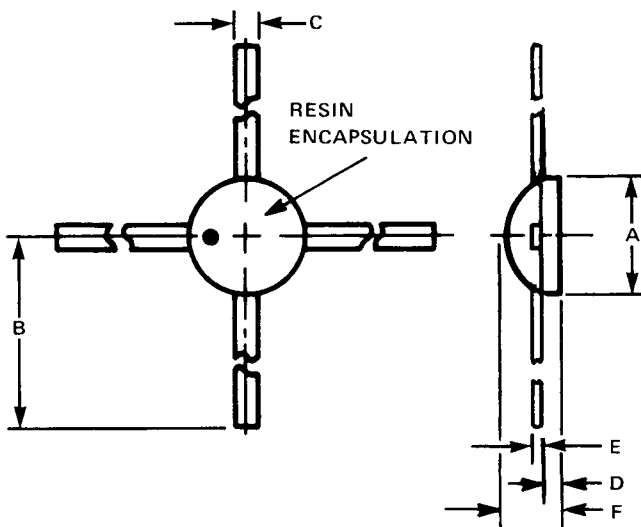
120



DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.051	0.055	1,30	1,40
B	0.040	0.050	1,02	1,27

C<sub>P</sub> = 0.13 pF Typical  
L<sub>S</sub> = 0.40 nH Typical

963 (MINI-QUAD)



DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.050	0.058	1,27	1,47
B	0.140	— —	3,55	— —
C	0.012	0.018	0,30	0,46
D	0.007	0.014	0,178	0,36
E	0.003	0.006	0,076	0,152
F	— —	0.035	— —	0,89

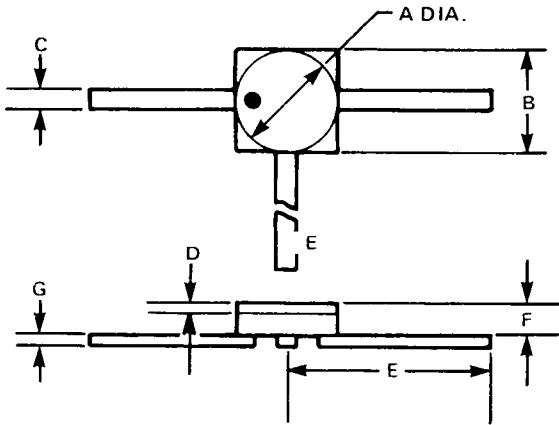
C<sub>P</sub> ~ 0.04 pF Typical



# Case Styles (Cont'd)

● DENOTES CATHODE

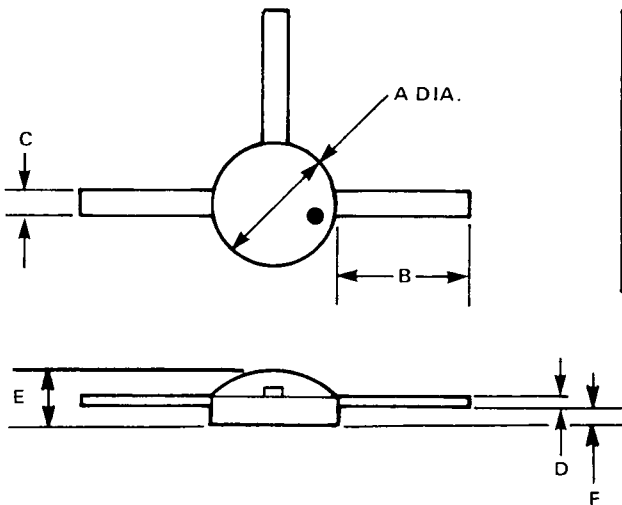
270



DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.094	0.102	2,39	2,59
B	0,094	0.102	2,39	2,59
C	0.018	0.022	0,46	0,56
D	0.005	0.008	0,13	0,20
E	0.200	— —	5,08	— —
F	0.030	0.040	0,75	1,02
G	0.003	0.006	0,08	0,15

C<sub>p</sub> ~ 0.12 pF Typical

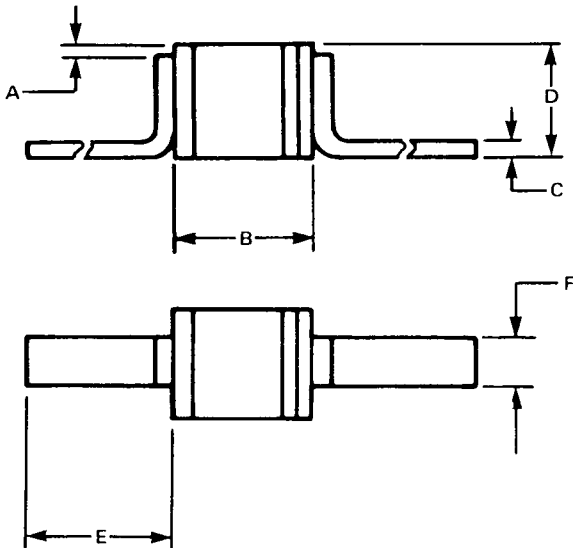
272



DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.090	0.110	2,29	2,75
B	0,090	0.110	2,29	2,75
C	0.018	0.022	0,46	0,56
D	0.003	0.006	0,08	0,15
E	— —	0.035	— —	0,09
F	— —	0.014	— —	0,36

C<sub>p</sub> ~ 0.10 pF Typical

276



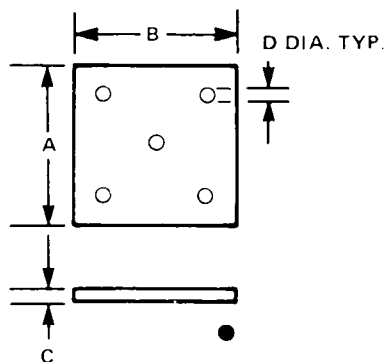
DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.010	0.020	0,254	0,058
B	0.040	0.050	1,02	1,27
C	— —	0.005	— —	0,127
D	0.051	0.055	1,29	1,39
E	0.200	— —	5,08	— —
F	0.019	0.021	0,483	0,533

C<sub>p</sub> = 0.13 pF Typical  
L<sub>S</sub> = 0.40 nH Typical

# Chip Styles

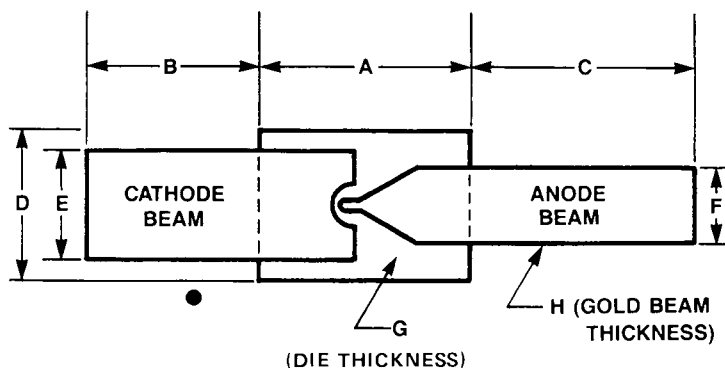
● DENOTES CATHODE

135



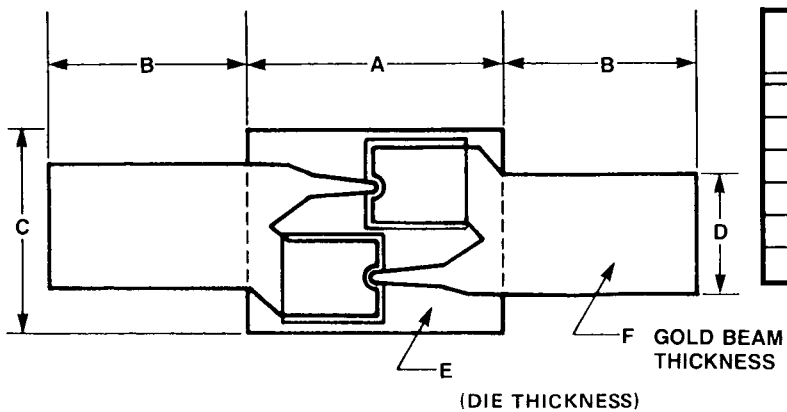
DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	.013	.017	.330	.431
B	.013	.017	.330	.431
C	.004	.006	.102	.152
D	.001	— —	.02	— —

1010



DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.010	0.012	0,25	0,30
B	0.012	— —	0,30	— —
C	0.010	— —	0,25	— —
D	0.006	0.008	0,15	0,20
E	0.005	0.006	0,12	0,15
F	0.004	0.005	0,10	0,12
G	0.003	0.004	0,07	0,10
H	0.0003 Nominal		0.012 Nominal	

1013



DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.0105	0.0125	0,26	0,32
B	0.007	— —	0,18	— —
C	0.0085	0.0105	0,22	0,26
D	0.005	0.006	0,13	0,15
E	0.003	0.004	0,07	0,10
F	0.0005 (Nominal)		0,012 (Nominal)	